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### **General Description**

Din-Tek Field Stop Trench IGBTs offer low switching losses, high energy efficiency and short circuit ruggedness.

It is designed for applications such as motor control, uninterrupted power supplies(UPS), general inverters.

#### **FEATURES**

- · High speed switching
- · High ruggedness, temperature stable behavior
- · Short Circuit Withstand Times 10us
- · Extremely enhanced avalanche capability

## DIM MILLIMETERS $5.00 \pm 0.20$ $20.85 \pm 0.30$ $3.00\pm0.20$ $2.00\pm0.20$ $1.20 \pm 0.20$ Н $20.10 \pm 0.70$ $0.60 \pm 0.02$ $14.70 \pm 0.20$ $2.00 \pm 0.10$ $2.40 \pm 0.20$ О $\phi 3.60 \pm 0.30$ $5.45\pm0.30$ $\phi 3.60 \pm 0.20$ $\phi$ 7.19 ± 0.10 TO-247

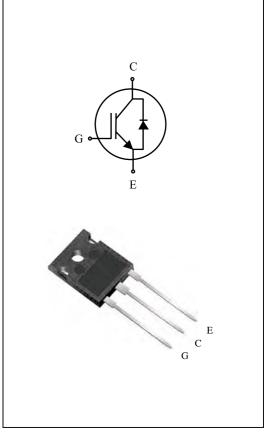
### **MAXIMUM RATING** (Ta=25 )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage		V <sub>GES</sub>	± 20	V
Collector Current	@Tc=25	- I <sub>C</sub>	50	A
Conector Current	@Tc=100	1 C	25	A
Pulsed Collector Current		I <sub>CM</sub> *	75	A
Diode Continuous Forward Current	@Tc=100	$I_F$	25	A
Diode Maximum Forward Current		$I_{FM}$	75	A
Maximum Power Dissipation	@Tc=25	P <sub>D</sub>	227	W
Waxiinuiii I owel Dissipation	@Tc=100	1 1 1	91	W
Maximum Junction Temperature		$T_{j}$	150	
Storage Temperature Range		$T_{stg}$	-55 to + 150	

<sup>\*</sup>Repetitive rating: Pulse width limited by max. junction temperature

#### THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R <sub>thJC</sub>	0.55	/W
Thermal Resistance, Junction to Case (DIODE)	R <sub>thJC</sub>	1.7	/W
Thermal Resistance, Junction to Ambient	R <sub>th JA</sub>	40	/W





## **ELECTRICAL CHARACTERISTICS** (Ta=25 )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static				•		•
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> =0V , I <sub>C</sub> =1mA	1200	-	-	V
Collector Cut-off Current	I <sub>CES</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V	-	-	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	± 100	nA
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{GE}=V_{CE}$ , $I_{C}=25$ mA	4.5	5.5	7.0	V
	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V, I <sub>C</sub> =25A	-	2.0	2.4	V
Collector-Emitter Saturation Voltage		$V_{GE}$ =15V, $I_{C}$ =25A, $T_{C}$ = 125	-	2.25	-	V
		V <sub>GE</sub> =15V, I <sub>C</sub> =50A	-	2.6	-	V
Dynamic				•		
Total Gate Charge	$Q_{g}$		-	160	-	nC
Gate-Emitter Charge	$Q_{ge}$	$V_{CC}$ =600V, $V_{GE}$ =15V, $I_{C}$ = 25A	-	25	-	nC
Gate-Collector Charge	$Q_{\mathrm{gc}}$		-	80	-	nC
Turn-On Delay Time	t <sub>d(on)</sub>		-	40	-	ns
Rise Time	t <sub>r</sub>		-	25	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{CC}$ =600V, $I_{C}$ =25A, $V_{GE}$ =15V, $R_{G}$ =10 Inductive Load, $T_{C}$ = 25	-	175	-	ns
Fall Time	$t_{\rm f}$		-	85	-	ns
Turn-On Switching Loss	E <sub>on</sub>		-	1.85	2.4	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	0.9	1.2	mJ
Total Switching Loss	E <sub>ts</sub>		-	2.75	3.6	mJ
Turn-On Delay Time	t <sub>d(on)</sub>		-	40	-	ns
Rise Time	t <sub>r</sub>		-	30	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	180	-	ns
Fall Time	t <sub>f</sub>	$V_{CC}$ =600V, $I_{C}$ =25A, $V_{GE}$ =15V, $R_{G}$ =10 Inductive Load, $T_{C}$ = 125	-	190	-	ns
Turn-On Switching Loss	E <sub>on</sub>		-	2.0	-	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	1.6	-	mJ
Total Switching Loss	E <sub>ts</sub>		-	3.6	-	mJ
Input Capacitance	C <sub>ies</sub>		-	2650	3450	pF
Ouput Capacitance	C <sub>oes</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz	-	115	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>		-	70	-	pF
Short Circuit Withstand Time	t <sub>sc</sub>	V <sub>CC</sub> =600V, V <sub>GE</sub> =15V, T <sub>C</sub> =100	10	-	-	μs



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## ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 25A	T <sub>C</sub> =25	-	2.4	3.0	V
			T <sub>C</sub> =125	-	2.5	-	
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F$ = 25A $di/dt$ = 200A/ $\mu$ s	T <sub>C</sub> =25	-	140	-	ns
			T <sub>C</sub> =125	-	180	-	
Diode Peak Reverse Recovery Current	$I_{rr}$		T <sub>C</sub> =25	-	13.5	-	A
			T <sub>C</sub> =125	-	16.0	-	A
Diode Reverse Recovery Charge	0		T <sub>C</sub> =25	-	1.05	-	μC
	$Q_{rr}$		T <sub>C</sub> =125	-	1.65	-	μ



Fig 1. Saturation Voltage Characteristics

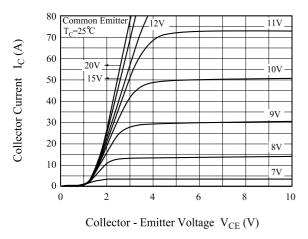


Fig 3. Saturation Voltage vs. Case Temperature

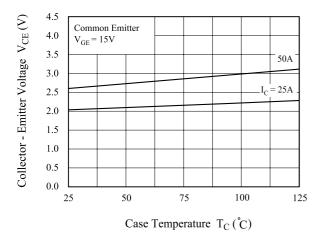


Fig 5. Saturation Voltage vs. V<sub>GE</sub>

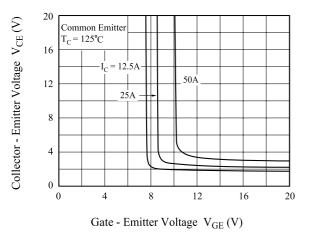


Fig 2. Saturation Voltage Characteristics

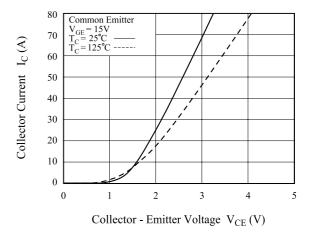


Fig 4. Saturation Voltage vs. V<sub>GE</sub>

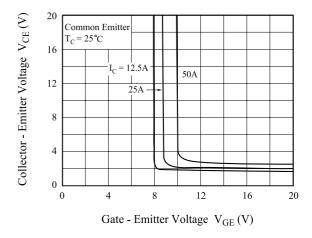
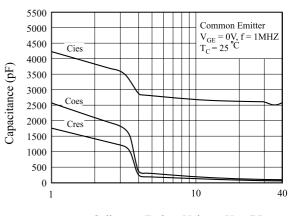


Fig 6. Capacitance Characteristics



Collector - Emitter Voltage  $V_{CE}(V)$ 



Fig 7. Turn-On Characteristics vs. Gate Resistance

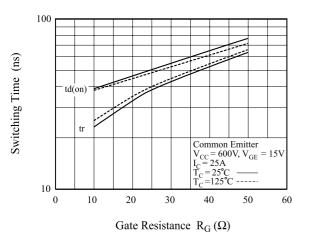


Fig 8. Turn-Off Characteristics vs. Gate Resistance

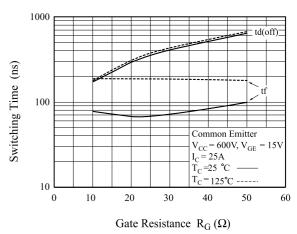


Fig 9. Switching Loss vs. Gate Resistance

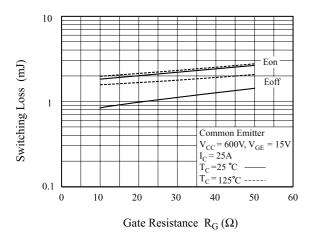


Fig 10. Turn-On Characteristics vs. Collector Current

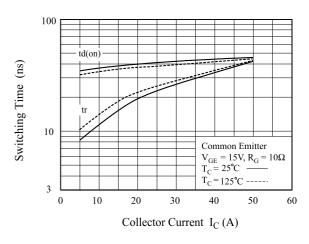


Fig 11. Turn-Off Characteristics vs. Collector Current

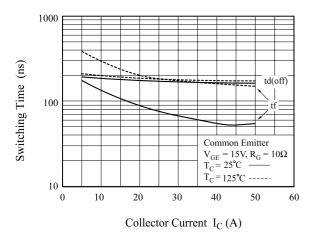


Fig 12. Switching Loss vs. Collector Current

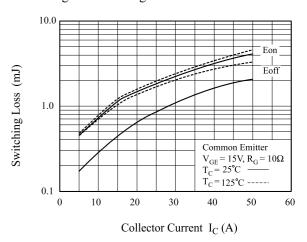




Fig 13. Gate Charge Characteristics

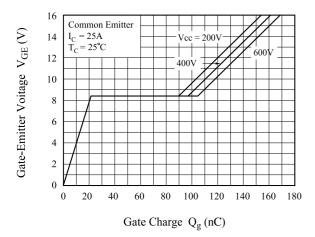
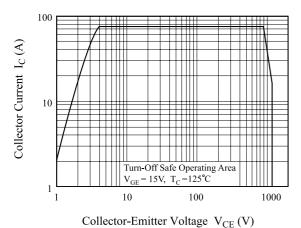


Fig 15. Turn-Off SOA



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Fig 14. SOA Characteristics

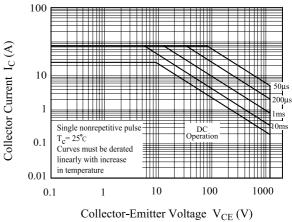
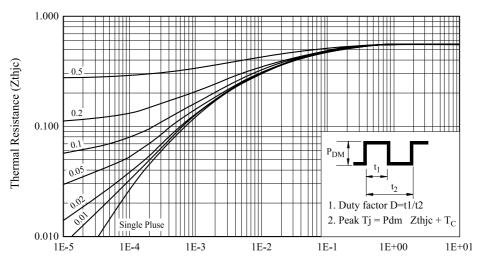


Fig 16. Transient Thermal Impedance of IGBT



Rectangular Pulse Duration (sec)



Fig 17. Forward Characteristics

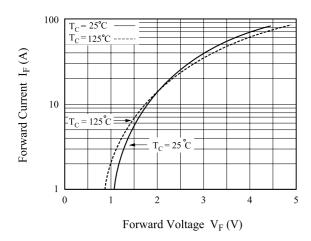


Fig 19. Reverse Recovery Time

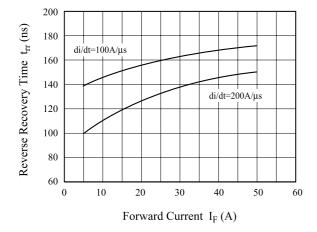


Fig 18. Reverse Recovery Current

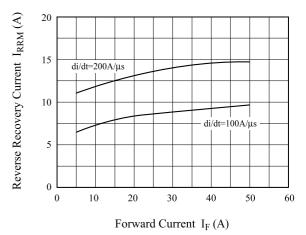




Fig 20. Switching Test Circuit

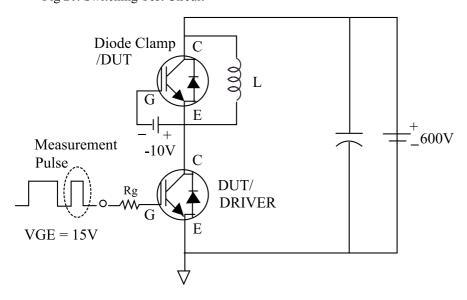
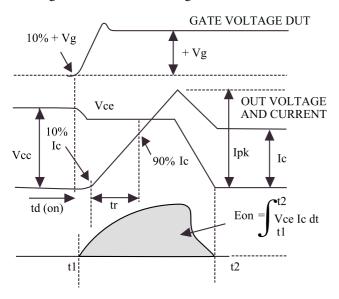


Fig 21. Definition Switching Time & Loss



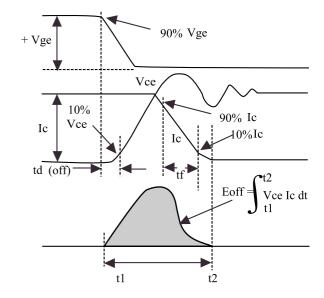
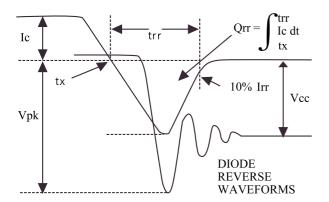
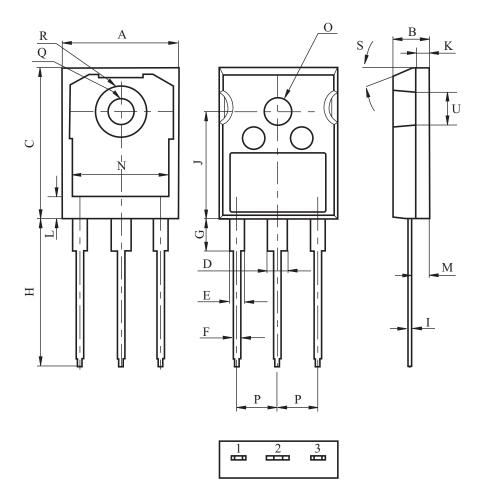


Fig 22. Definition Diode Switching Time





# TO-247 (High Voltage)



DIM	MILLIMETERS
A	$15.90 \pm 0.30$
В	$5.00 \pm 0.20$
С	$20.85 \pm 0.30$
D	$3.00 \pm 0.20$
Е	$2.00 \pm 0.20$
F	$1.20 \pm 0.20$
G	Max. 4.50
Н	$20.10 \pm 0.70$
Ι	$0.60 \pm 0.02$
J	$14.70 \pm 0.20$
K	$2.00 \pm 0.10$
L	$3.19\pm0.20$
M	$2.40 \pm 0.20$
N	13.26
О	$\phi 3.70 \pm 0.20$
P	$5.45 \pm 0.30$
Q	$\phi 3.60 \pm 0.20$
R	$\phi$ 7.19 $\pm$ 0.10
S	20°
U	4.57
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